Data sheet Cella 3BB

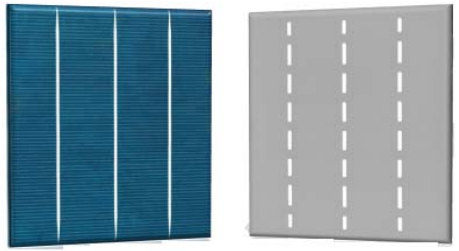
Specification

Technical Data sheet

DMS loc.:	Rev.:	Doc.:	Rev. date:	Doc. owner:	Physical location:
8100.03E	03	FO	28-05-2013	QA	

Cell Type: H-pattern / segmented Back-side
Configuration 01

Description



Cell Layout _GEN_03

Dimensions		
Feature	**Qualification**	**Permitted Deviation**
Outer dimensions	156mm x 156mm	± 0.5 mm
Cell thickness nominal as ordered	on wafer level	± 30 µm
Bow	Cell placed on flat surface sunny side up. Distance between centre of cell and flat surface	<= 2.5mm.

Front surface		
Width of busbar	1.4 mm	± 0.1 mm
Number of busbar	3	
Distance between centre busbar and outer busbar	52.0	± 0.2 mm
Material of busbar	Silver	

Back surface		
Width of busbar	2.5 mm	± 0.5 mm
Number of segments	3	
Length of segment interruption	25 mm	± 0.5 mm
Number of busbar	3	
Distance between centre busbar and outer busbar	52.0	± 0.2 mm
Material of busbar	Silver	
Material of the surrounding parts of the back surface of the cell	Aluminum	

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Electrical properties		
Power	Power classes according to P_{max} at standard test conditions (STC, AM 1.5, 1000 W/m², 25°C) Accuracy of measurement ± 1.5% relative to ISE certified reference cell	Divided in classes, see below
Reverse bias criteria	Reverse dark measurement V_{bias} = -12 V allowed current V_{bias} = -6 V allowed current measurement accuracy ± 2%	 I bias <2.0 A, I bias <0.4 A.
Shunt resistivity	(Dark I-V measurement) at 0V	R_{sh} > 15 Ohm

Typical data at STC (non encapsulated cells)*

Cellclass	Pmpp(W)	Efficiency(%)	Voc(mV)	Isc(A)
S156PS375	3.75	15.40	602	8.18
S156PS380	3.80	15.60	605	8.22
S156PS385	3.85	15.80	607	8.25
S156PS390	3.90	16.00	609	8.28
S156PS395	3.95	16.20	612	8.33
S156PS400	4.00	16.40	614	8.38
S156PS405	4.05	16.60	616	8.41
S156PS410	4.10	16.80	618	8.45
S156PS415	4.15	17.00	620	8.49
S156PS420	4.20	17.20	622	8.53
S156PS425	4.25	17.40	625	8.56
S156PS430	4.30	17.60	627	8.60